

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Attorney Docket Number	23-65037-09
Application Number	10/581,281
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First Named Inventor	Larry C. Olsen
Art Unit	1795
Examiner Name	Shannon M. Gardner

U.S. PATENT DOCUMENTS

Copies of U.S. Patent documents do not need to be provided, unless requested by the Patent and Trademark Office. For patents, provide the patent number and the issue date. For published U.S. applications, provide the publication number and the publication date. For unpublished pending patent applications, provide the application number and the filing date and submit a copy.

Examiner's Initials*	Cite No. (optional)	Number	Date	Name of Applicant or Patentee
		4,125,122	11/1978	Stachurski

FOREIGN PATENT DOCUMENTS

Examiner's Initials*	Cite No. (optional)	Country	Number	Date	Name of Applicant or Patentee

OTHER DOCUMENTS

Examiner's Initials*	Cite No. (optional)	Böttner, H., "Thermoelectric Micro Devices: Current State, Recent Developments and Future Aspects for Technological Progress and Applications," <i>Proc. 21st Int. Conf. Thermoelectronics, Long Beach, CA</i> , pp. 511-518 (August 25-29, 2002).
		Final Office action from the U.S. Patent and Trademark Office for U.S. Patent Application No. 10/726,744, dated April 13, 2009.
		Final Office action from the U.S. Patent and Trademark Office in U.S. Patent Application No. 10/727,062, dated July 20, 2009.
		Kim, D.-H. et al., "Effect of deposition temperature on the structural and thermoelectric properties of bismuth telluride thin films grown by co-sputtering," <i>Thin Solid Films</i> , Vol. 510, pp. 148-153 (2006).
		Nurnus, J. et al., "Structural and Thermoelectric Properties of Bi ₂ Te ₃ Based Layered Structures," <i>Proc. 19th Int. Conf. Thermoelectrics</i> , Cardiff, U.K., pp. 236-240 (August 25-29, 2000).
		Office action from the U.S. Patent and Trademark Office in U.S. Patent Application No. 11/004,611, dated August 3, 2009.
		Sun, C.W. et al., "Crystallization behavior of non-stoichiometric Ge-Bi-Te ternary phase change materials for PRAM application," <i>J. Phys. Condens. Matter</i> , Vol. 19, 446004, 9 pages (2007).

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